

# MCR221-5, MCR221-7, MCR221-9

### SILICON CONTROLLED RECTIFIERS

### **FEATURES**

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.

#### MAXIMUM RATINGS.

Rating	Symbol	Value	Unit
Peak repetitive forward and reverse off-state voltage (1)			
MCR221-5	$V_{DRM}$	300	Volts
MCR221-7	$V_{RRM}$	500	VOILS
MCR221-9		700	
On-state RMS current			A
(180° conduction angles), T <sub>C</sub> = 90°C)	I <sub>T(RMS)</sub>	16	Amps
Average on-state current	I <sub>T(AV)</sub>	10	Amps
Peak non-repetitive surge current	1		Amns
(1/2 cycle, sine wave 60Hz, $T_J = 125$ °C)	I <sub>TSM</sub>	160	Amps
Circuit fusing (t = $8.3$ ms, $T_J$ = $-40$ to $+125$ °C)	I <sup>2</sup> t	100	A <sup>2</sup> s
Forward peak gate power	$P_{GM}$	20	Watts
Forward average gate power	$P_{G(AV)}$	0.5	Watts
Forward peak gate current	I <sub>GM</sub>	2.0	Amps
Operating junction temperature range	T <sub>J</sub>	-40 to 125	°C
Storage temperature range	$T_{stg}$	-40 to 150	°C

## THERMAL CHARACTERISTICS

	Characteristic	Symbol	Max	Unit
Ì	Thermal resistance, junction to case	R <sub>eJC</sub>	1.5	°C/W

#### **ELECTRICAL CHARACTERISTICS** (T<sub>1</sub> = 25°C unless otherwise specified)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	1			11		
Peak repetitive forward or reverse blocking current						
$(V_{AK} = rated V_{DRM} or V_{RRM}, gate open)$	T <sub>J</sub> = 25°C		-	-	10	μΑ
	T <sub>J</sub> = 125°C	I <sub>DRM</sub> , I <sub>RRM</sub>	-	-	2.0	mA
ON CHARACTERISTICS						
Peak forward on-state voltage						Valta
$(I_{TM} = 32A \text{ peak, pulse width} \le 1 \text{ms, duty cycle} \le 2\%)$		$V_{TM}$	-	-	1.7	Volts
Gate trigger current (continuous dc)						^
$(V_D = 12Vdc, R_L = 50ohms)$		I <sub>GT</sub>	-	5.0	30	mA
Gate trigger voltage (continuous dc)						
$(V_D = 12Vdc, R_L = 50ohms)$	T <sub>C</sub> = 25°C	$V_{GT}$	-	0.7	1.5	Volts
	T <sub>C</sub> = -40°C		-	-	2.5	
Gate non-trigger voltage						Valta
$(V_D = Rated V_{DRM}, R_L = 50ohms)$	T <sub>C</sub> = 125°C	$V_{GD}$	0.2	-	-	Volts



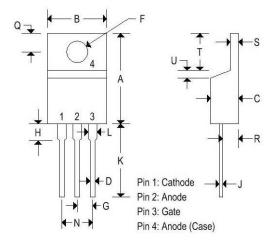
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ON CHARACTERISTICS						
Holding current						
(V <sub>D</sub> = 12Vdc)	T <sub>C</sub> = 25°C	I <sub>H</sub>	-	6	40	mA
	T <sub>C</sub> = -40°C		-	-	60	
Turn-on time						
$(I_{TM} = 16A, I_{GT} = 40 \text{mAdc}, V_D = \text{rated } V_{DRM})$		t <sub>gt</sub>		1.0	-	μs
Turn-off time						
$(I_{TM} = 16A, I_R = 16A, V_D = rated V_{DRM})$	$T_C = 25^{\circ}C$	tq	-	15	-	μs
	T <sub>J</sub> = 125°C		-	35	-	
DYNAMIC CHARACTERISTICS						
Critical rate of rise of off state voltage		al / al.e.				1//
(V <sub>D</sub> = rated V <sub>DRM</sub> , exponential waveform)	T <sub>J</sub> = 125°C	dv/dt	-	50	-	V/µs

#### **MECHANICAL CHARACTERISTICS**

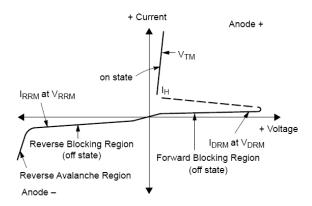
Case:	TO-220AB
Marking: Body painted, alpha-numeric	
Pin out:	See below



	TO-220 <b>A</b> B					
	Inches		Millim	neters		
	Min	Max	Min	Max		
Α	0.575	0.620	14.600	15.750		
В	0.380	0.405	9.650	10.290		
С	0.160	0.190	4.060	4.820		
D	0.025	0.035	0.640	0.890		
F	0.142	0.147	3.610	3.730		
G	0.095	0.105	2.410	2.670		
Н	0.110	0.155	2.790	3.930		
J	0.014	0.022	0.360	0.560		
K	0.500	0.562	12.700	14.270		
L	0.045	0.055	1.140	1.390		
N	0.190	0.210	4.830	5.330		
Q	0.100	0.120	2.540	3.040		
R	0.080	0.110	2.040	2.790		
S	0.045	0.055	1.140	1.390		
Т	0.235	0.255	5.970	6.480		
U	-	0.050	-	1.270		
٧	0.045	120	1.140	r <b>a</b>		
Z	-	0.080		2.030		



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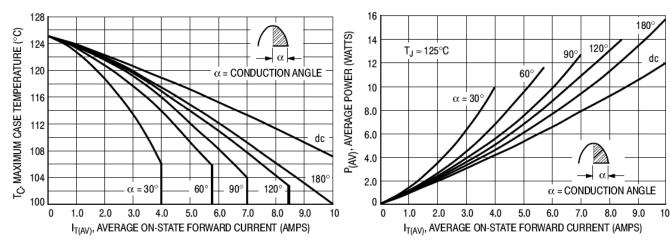


Figure 1. Average Current Derating

Figure 2. Maximum On-State Power Dissipation



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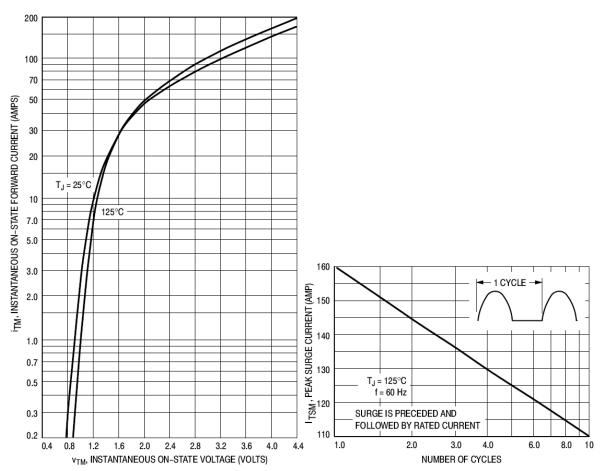


Figure 3. On-State Characteristics

Figure 4. Maximum Non-Repetitive Surge Current

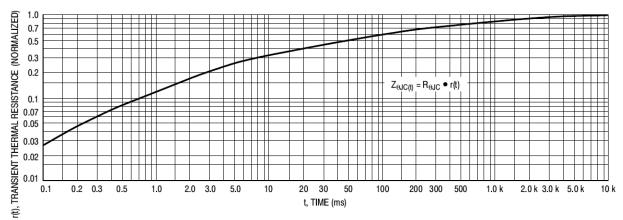


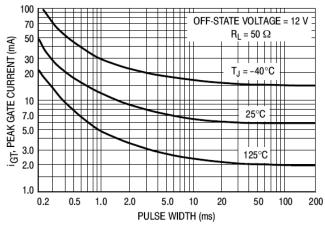
Figure 5. Thermal Response



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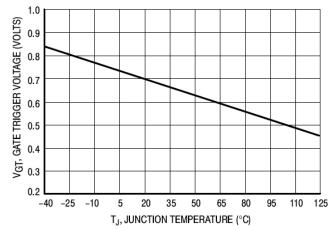
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100 (W) 100 (W

Figure 6. Typical Gate Trigger Current versus Pulse Width

Figure 7. Typical Gate Trigger Current versus Junction Temperature



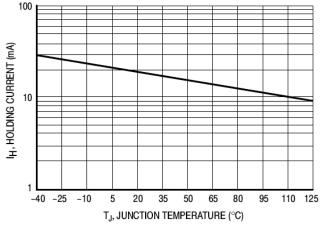


Figure 8. Typical Gate Trigger Voltage versus Junction Temperature

Figure 9. Typical Holding Current versus Junction Temperature